



Cell listing

High speed/high frequencies analog I/O's

Contact: BD@sofics.com

Sofics has verified its TakeCharge ESD protection clamps on a wide variety of processes, including CMOS, SOI and FinFET technologies across various fabs and foundries. The ESD clamps are silicon and product proven in more than 3000 mass produced IC-products. The cells provide competitive advantage through improved yield, reduced silicon footprint and enable high speed, higher operating voltages and complex architectures. Higher robustness level for a wide range of ESD/EOS and other specifications are available upon request.

The devices described in this document can be used for the protection of various high speed pins

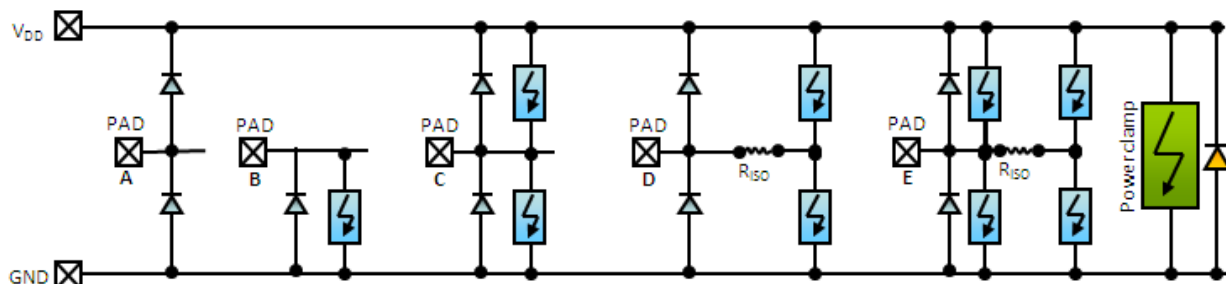
Analog I/O's with low capacitive loading

The following table provides an overview of the Sofics low capacitance ESD clamps. Most cells are proven in different flavours; the solutions are highly portable to other processes and different flavors. Furthermore, the cells can easily be adopted for other ESD protection levels and can be further customized to ensure compatibility with specific metal schemes and I/O pitch. Cells for other voltage domains can be provided as well.

The capacitance number includes metallization up to the bus, and thus not include the bond pad. Therefore, a different metallization option or different bus routing can lead to slightly capacitive loading, but Sofics will take care of the optimization for you.

Please discuss your specific requirement with our sales person at bd@sofics.com.

The Sofics ESD cells cover all types of protection concepts and approaches as detailed in the figure below.



Different pad types available in the solution set from Sofics. For each power domain a power clamp is available. For the IO's several pad-types exist.

Foundry	Node	Voltage domain [V]	Type clamp	Leakage	Cap [fF]	ESD performance	Info
TSMC	28	0.85	A	<50nA	<100	2 kV HBM, 200 V MM	Overvoltage tolerant, includes CDM clamp
TSMC	28	1.8	A	<50nA	<100	2 kV HBM, 200 V MM	Overvoltage tolerant
TSMC	28	3.3	A	<50nA	<100	2 kV HBM, 200 V MM	
TSMC	28	3.3	A	<40pA	10.2	200 V HBM	Ultra-low capacitive dual diode
TSMC	40	0.9	A	<100pA	<100	2.8 kV HBM, 230 V MM	Dual diode protection
TSMC	40	1.1	A	<100pA	<100	2.8 kV HBM, 230 V MM	Dual diode protection
TSMC	40	1.2	A	<100pA	<100	2.8 kV HBM, 230 V MM	Dual diode protection
TSMC	40	1.8	A	<100pA	<100	2.8 kV HBM, 230 V MM	Dual diode protection
TSMC	40	1.8	B	<100pA	66.6	2.1 kV HBM, 210 V MM	Overvoltage tolerant

TSMC	40	3.3	A	<100pA	<100	2.8 kV HBM, 230 V MM	Dual diode protection
TSMC	65	1	A	<1nA	<100	4 kV HBM	Dual diode protection , Circuit Under Pad
TSMC	65	1	B	<10nA	~60	3 kV HBM	Overvoltage tolerant, Circuit Under Pad
TSMC	65	1.2	A	<1nA	<100	4 kV HBM	Dual diode protection, Circuit Under Pad
TSMC	65	1.8	A	<1nA	<100	4 kV HBM	Dual diode protection, Circuit Under Pad
TSMC	65	2.5	A	<1nA	<100	4 kV HBM	Dual diode protection
TSMC	65	3.3	A	<1nA	<100	4 kV HBM	Dual diode protection, Circuit Under Pad
TSMC	90	3.3	B	<0.5nA	<100	2 kV HBM, 100 V MM	Overvoltage tolerant
TSMC	130	1.2	B	<50pA	<100	4 kV HBM, 250 V MM	
TSMC	130	1	B	<50pA	<100	4 kV HBM, 250 V MM	
TSMC	130	3.3	B	<50pA	<100	4 kV HBM, 250 V MM	
TSMC	130	1.2	A	<1nA	<100	3.2 kV HBM, 240 V MM	Dual diode protection
TSMC	130	1.2	B	<10nA	<50	2.8 kV HBM, 220 V MM	Overvoltage tolerant
TSMC	130	1.2	C	<50pA	<100	3.8 kV HBM, 290 V MM	Full local protection
TSMC	130	3.3	A	<1nA	<100	3.2 kV HBM, 240 V MM	Dual diode protection
TSMC	130	3.3	B	<50pA	<100	3.8 kV HBM, 290 V MM	
TSMC	130	3.3	C	<50pA	<100	3.8 kV HBM, 290 V MM	Full local protection
UMC	130	1.2	A	<10nA	109	2 kV HBM, 200 V MM	Dual diode protection
UMC	130	3.3	A	<10nA	109	2 kV HBM, 200 V MM	Dual diode protection
GF	65	1	A	<50nA	<50	2 kV HBM, 200 V MM	Ultra-low capacitive dual diode replacement
GF	65	1.2	A	<50nA	<50	2 kV HBM, 200V MM	Ultra-low capacitive dual diode replacement
GF	65	1.5	A	<50nA	<50	2 kV HBM, 200 V MM	Ultra-low capacitive dual diode replacement
GF	65	1.8	A	<50nA	<50	2 kV HBM, 200 V MM	Ultra-low capacitive dual diode replacement
GF	65	2.5	A	<50nA	<50	2 kV HBM, 200 V MM	Ultra-low capacitive dual diode replacement
GF	65	3.3	A	<50nA	<50	2 kV HBM, 200 V MM	Ultra-low capacitive dual diode replacement

About CDM

It is noted that the listed cells do not contain a CDM specification. CDM levels for a stand alone cell are technically not relevant. Notwithstanding this, all ESD solutions provided by Sofics are optimized for CDM performance. The CDM design is based on

- ESD clamps with trigger speed enhancements and specific CDM clamp circuits
- VF-TLP analysis with fast rise time and short pulses
- Evaluation of the sensitivity of the (functional operation) circuitry
- Analysis of the different voltage domains and bus architecture
- General ESD/CDM expertise

The CDM performance of the Sofics' protected pins in actual integrated circuits routinely pass 500V, and 250-300V for high speed pins.

About porting

All cells can be ported to any CMOS process, though the actual numbers (leakage, capacitance, area) may vary slightly.

For typical behavior, no additional silicon validation is required. Typical behavior includes achieving ESD levels. The porting is based on

- Measured data on selected processes and foundries
- Porting experience of over 50 processes
- PDK data

For optimization of leakage and/or capacitance, an additional silicon validation run may be advisable, depending on the required level and accuracy.

About Sofics Sofics (www.sofics.com) is the world leader in IP for robust IC design. Its patented technology is proven in more than 3000 IC designs across all major foundries and process nodes. IC companies of all sizes rely on Sofics for off-the-shelf or custom-crafted solutions to protect overvoltage IOs, other non-standard IOs, and high-voltage ICs, including those that require system-level protection on the chip for ESD, EOS, EMC, radiation or other specifications.

Sofics technology produces smaller I/O's than any generic ESD configuration. It also permits twice the IC performance in high-frequency and high-speed applications. Sofics ESD solutions and service begin where the foundry design manual ends.

Our service and support

Our business models include

- Single-use, multi-use or royalty bearing license for ESD clamps
- Services to customize ESD protection
 - Enable unique requirements for Latch-up, ESD, EOS
 - Layout, metallization and aspect ratio customization
 - Area, capacitance, leakage optimization
- Transfer of individual clamps to another target technology
- Develop custom ESD clamps for foundry or proprietary process
- Debugging and correcting an existing IC or I/O
- ESD testing and analysis

Notes

As is the case with many published ESD design solutions, the techniques and protection solutions described in this data sheet are protected by patents and patents pending and cannot be copied freely. PowerQubic, TakeCharge and Sofics are trademarks of Sofics BVBA.

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